

AMENDMENT OF SPECIFICATION

Please insert in Specification on page 12, line 14,
between first paragraph and second paragraph the
following paragraph:

To be more clear, as to the insulating layer and intermetal dielectric layer materials, they are comprised of: silicon dioxide, silicon oxide, undoped silicate glass, Fluorine doped Oxide, Carbon-doped Oxide, Organic based low-k dielectric, and porous low-k dielectric, where the IMD, inter-metal dielectric, film thickness is in a range approximately from 0.2 to 2 microns. Furthermore, the bi-layered hard mask is comprised of the following sets of two layered materials:

HM1 HM2

USG / SiC or SiN

USG / SiC

USG / SiC

USG / SiC

wherein USG, is undoped silicate glass for HM1 layer, and is the hard mask top layer, which can be a conventional SiO₂ film, of thickness in the range from 1000 to 2000 Angstroms. The HM2, is the hard mask bottom layer, and which is a dielectric layer with etch selectivity of ~3-5 for HM1 etch, and therefore, the HM1 etch stops on this bottom HM2 layer.